

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = 25^\circ\text{C}$
-30V	45m Ω @ $V_{GS} = -10\text{V}$	-4.8A
	80m Ω @ $V_{GS} = -4.5\text{V}$	-3.5A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

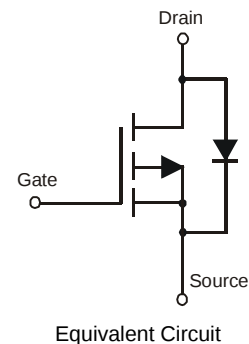
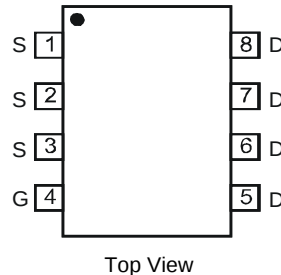
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe.
Solderable per MIL-STD-202, Method 208 
- Weight: 0.008 grams (approximate)

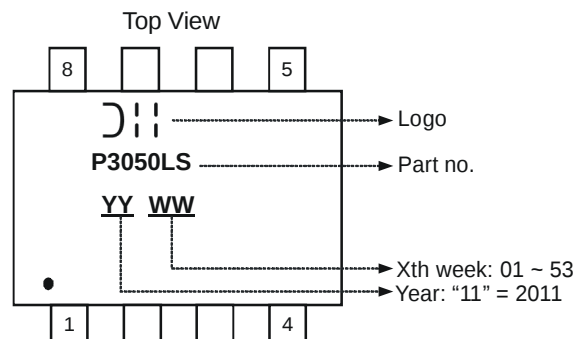


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3050LSS-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage (Note 4)			V _{GSS}	±25	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = 25°C T _A = 70°C	I _D	-4.8 -3.8	A
	t < 10s	T _A = 25°C T _A = 70°C	I _D	-6.3 -4.9	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-3.0	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	-30	A

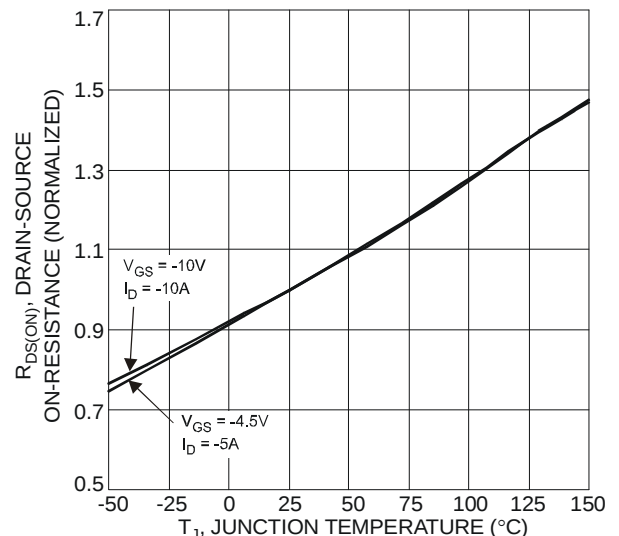
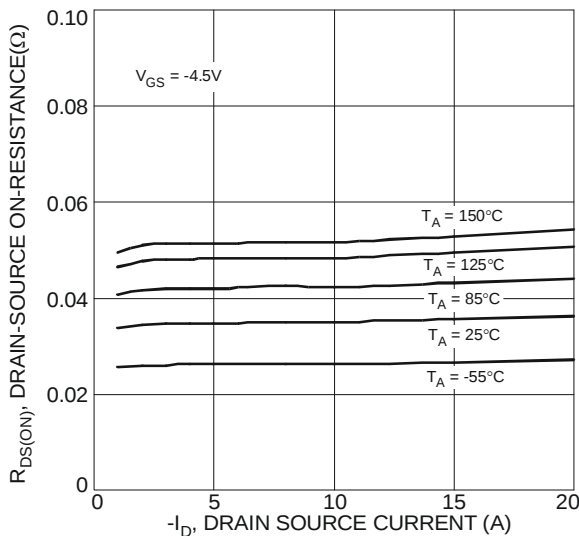
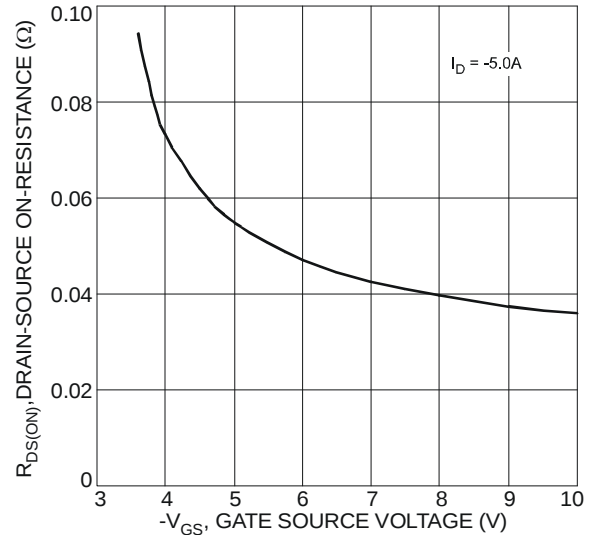
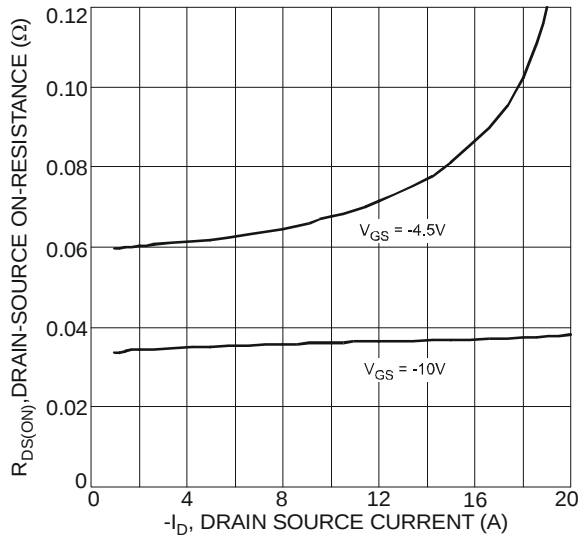
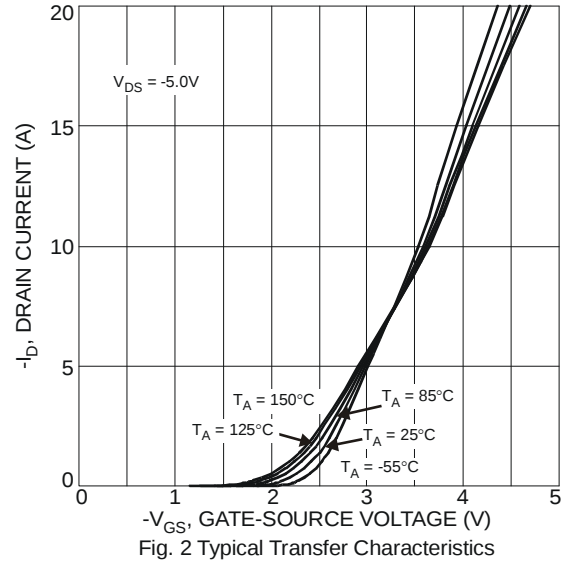
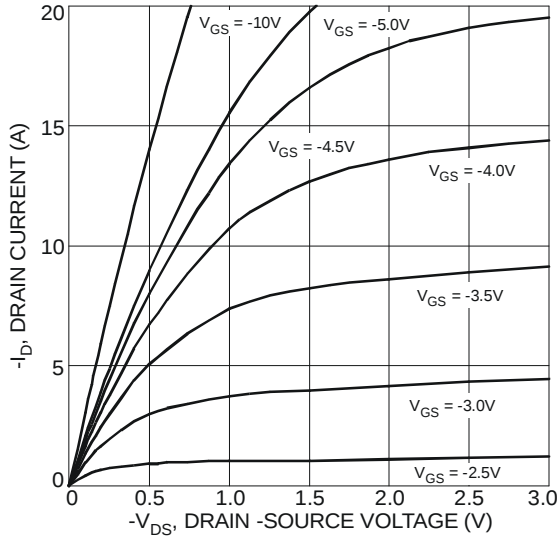
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = 25°C	P _D	1.7	W
	T _A = 70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	73	°C/W
	t < 10s		37	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	-	-2.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	36	45	mΩ	V _{GS} = -10V, I _D = -6A
		-	61	80		V _{GS} = -4.5V, I _D = -5A
Forward Transfer Admittance	Y _{fs}	-	4.8	-	S	V _{DS} = -10V, I _D = -5.3A
Diode Forward Voltage	V _{SD}	-	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1.7A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	620	-	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	83	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	62	-	pF	
Gate resistance	R _g	-	10.8	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	-	5.1	-	nC	V _{DS} = -15V, I _D = -6A
Total Gate Charge (V _{GS} = -10V)	Q _g	-	10.5	-	nC	
Gate-Source Charge	Q _{gs}	-	1.8	-	nC	
Gate-Drain Charge	Q _{gd}	-	1.9	-	nC	
Turn-On Delay Time	t _{D(on)}	-	6.8	-	ns	V _{DD} = -15V, V _{GS} = -10V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _r	-	4.9	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	
Turn-Off Fall Time	t _f	-	12.4	-	ns	I _F = 12A, di/dt = 500A/μs
Reverse Recovery Time	t _{rr}	-	14	-	ns	
Reverse Recovery Charge	Q _{rr}	-	11	-	nC	

- Notes: 4. AEC-Q101 V_{GS} maximum is ±20V
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.



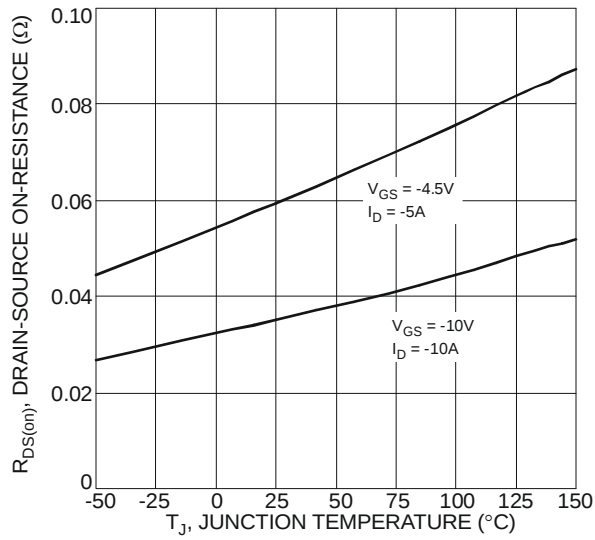


Fig. 7 On-Resistance Variation with Temperature

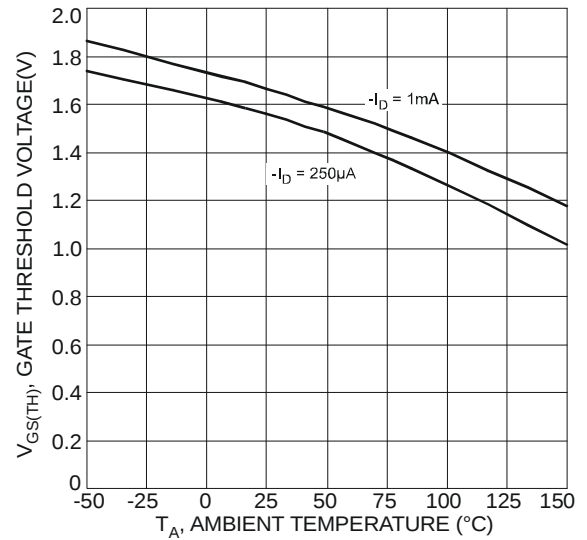


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

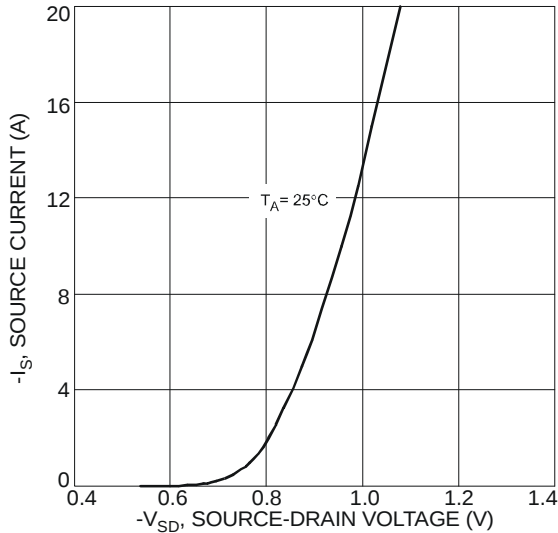


Fig. 9 Diode Forward Voltage vs. Current

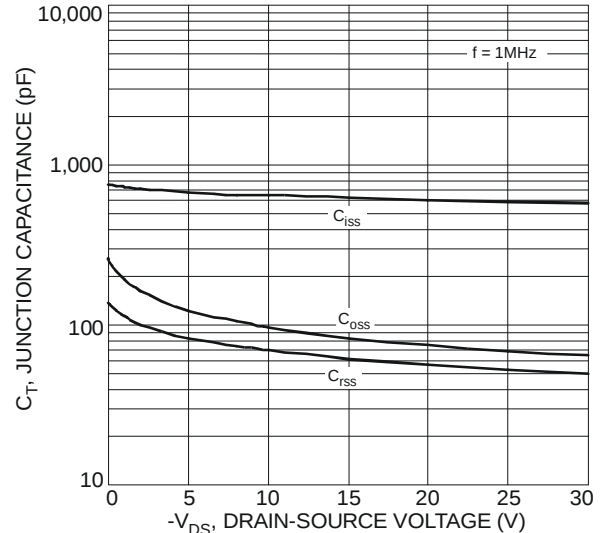


Fig. 10 Typical Junction Capacitance

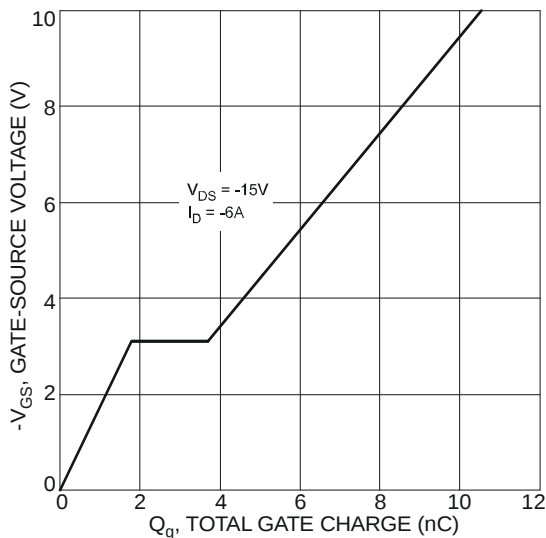


Fig. 11 Gate-Charge Characteristics

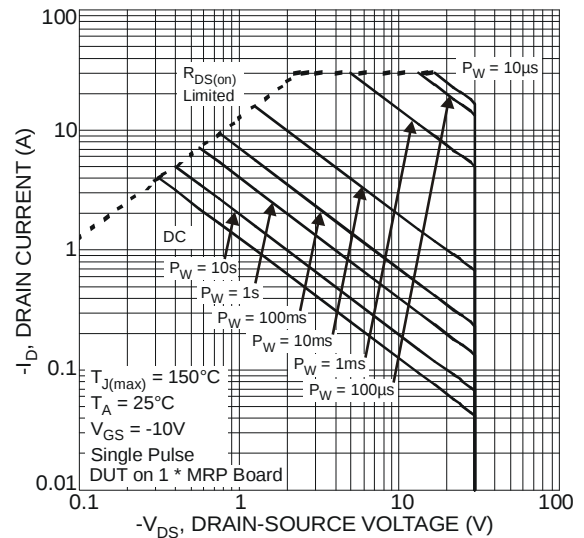
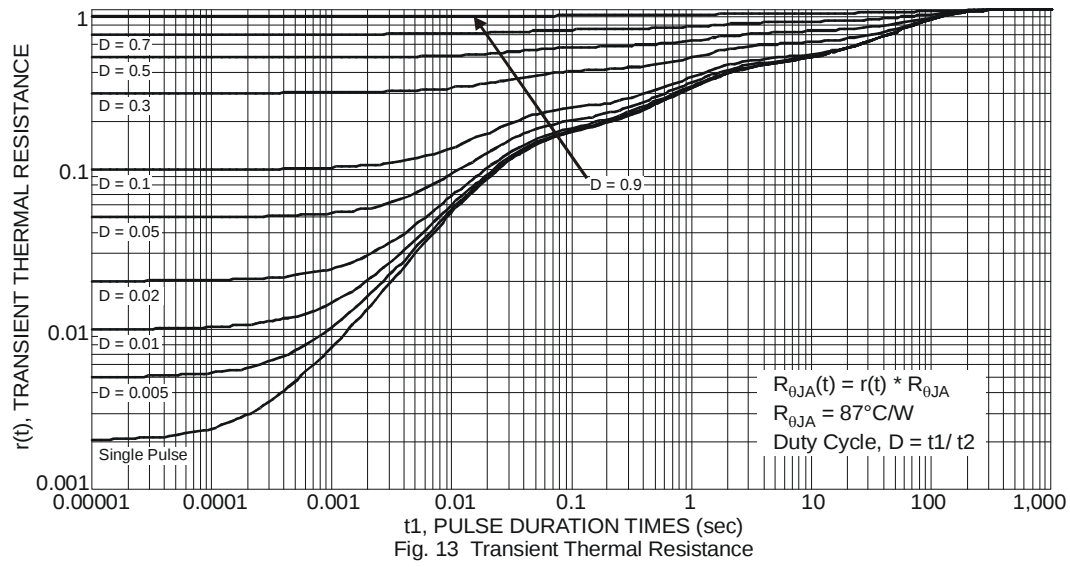
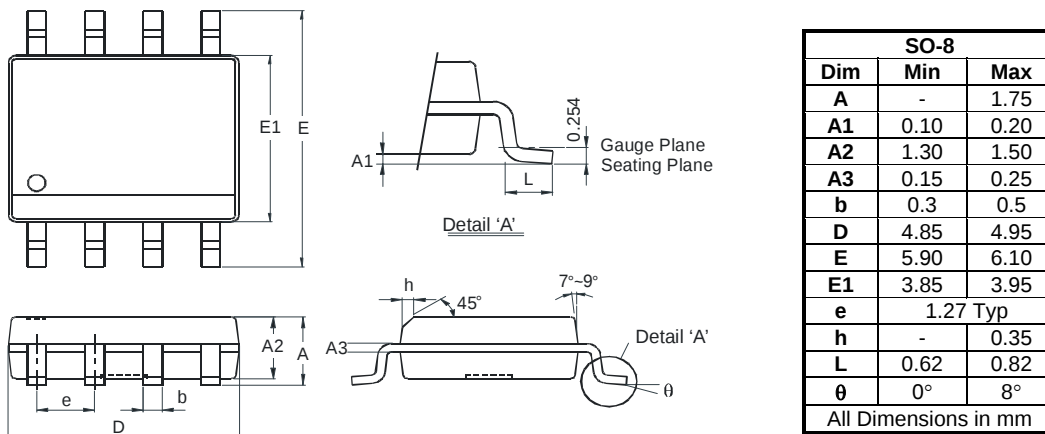


Fig. 12 SOA, Safe Operation Area



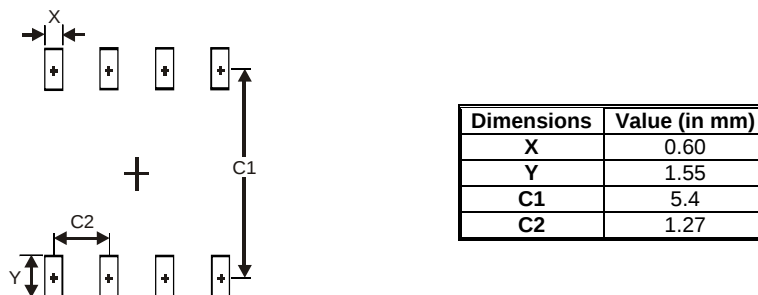
Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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